

L Number	Hits	Search Text	DB	Time stamp
-	92	("257/168").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 17:40
-	312	("257/173").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:15
-	9	((("257/168").CCLS.) and (("257/173").CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:15
-	4	plurality adj2 bipolar adj transistor.clm. and esd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:16
-	36	((("257/168").CCLS.) or (("257/173").CCLS.)) and esd and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:17
-	40	(plurality adj2 bipolar adj transistor.clm. and esd) or (((("257/168").CCLS.) or (("257/173").CCLS.)) and esd and bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:22
-	547	resistor and esd and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:23
-	117	resistor and esd and ((parallel or lateral\$2) near3 bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:34
-	152	charpentier.in.	EPO	2002/02/05 20:35
-	395	((("257/168").CCLS.) or (("257/173").CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 10:57
-	166	((("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:43
-	97	((("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:47
-	94	((("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:48
-	94	((("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:51

-	93	((("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load))and bipolar.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:51
-	93	((("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load))and bipolar.ti,ab. and (ic or integrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:52
-	93	((("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load))and bipolar.ti,ab. and (ic or integrated adj circuit) and bus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:54
-	93	((("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load)) and bipolar.ti,ab. and (ic or integrated adj circuit) and bus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:54
-	31	((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect\$3.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:57
-	20	(((((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 08:57
-	16	(((((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2 transistor) and resist\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 09:14
-	3	5043782.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 09:16
-	2	5708550.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 09:15
-	2	jp-61292351\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 09:16
-	395	((("257/168") or ("257/173")).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:37
-	0	("L3 and esd adj2 protection.ti,ab.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 10:58

-	29	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 10:58
-	7	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 10:59
-	0	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab. and plurality adj2 bipolar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 10:59
-	0	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab. and plurality adj2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:00
-	15	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:00
-	12	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar adj transistor and resist\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:02
-	5	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar adj transistor and resist\$3 and parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:02
-	3	((("257/168") or ("257/173")).CCLS.) and esd adj protection.ti,ab. and bipolar adj transistor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:48
-	131	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 11:49
-	1	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and plurality adj2 (bipolar or transistor) and resist\$3 and parallel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 14:06
-	12	esd adj protection.ti,ab. and ((advantage or purpose) nearl0 \$3bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 14:08
-	1	("0708550").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 15:07
-	2	("5708550").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 15:35
-	7	((("5043782") or ("5708550") or ("6268639") or ("5329143") or ("6172404") or ("5623387") or ("5272371")).PN.	USPAT	2002/02/06 15:20

-	5	((("5043782") or ("5708550") or ("6268639") or ("5329143") or ("6172404") or ("5623387") or ("5272371")).PN.) and (base adj region and bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 15:21
-	0	("esd adj protection.ti,ab and bipolar adj transistor.ti,ab. and path").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 15:35
-	0	("esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and path").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 15:36
-	48	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and path	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 15:38
-	17	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab. and current adj path	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 15:40
-	15	bipolar adj transistor and esd adj protection and (increase near12 path)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 16:49
-	12	bipolar adj transistor and esd adj protection and ((base near10 (surround\$3 or enclos\$3)) near10 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:01
-	710	bipolar adj transistor.ti,ab. and ((base near10 (surround\$3 or enclos\$3)) near10 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:04
-	506	bipolar adj transistor.ti,ab. and ((base near5 (surround\$3 or enclos\$3)) near5 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:05
-	334	bipolar adj transistor.ti,ab. and ((base near3 (surround\$3 or enclos\$3)) near3 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:05
-	2	bipolar adj transistor.ti,ab. and ((base near3 (surround\$3 or enclos\$3)) near3 (emitter or collector)) and esd.ti,ab. and protection.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:07
-	5	bipolar adj transistor.ti,ab. and ((base near4 (surround\$3 or enclos\$3)) near4 (emitter or collector)) and (electrostatic adj discharge or esd).ti,ab. and protection.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:10
-	430	bipolar adj transistor.ti,ab. and ((base near4 (surround\$3 or enclos\$3)) near4 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:11
-	6	bipolar adj transistor.ti,ab. and ((base near4 (surround\$3 or enclos\$3)) near4 (emitter or collector)) and (esd with protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:32

-	997	("257/355").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:33
-	95	((("257/355").CCLS.) and esd adj protection and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:42
-	4	((("257/355").CCLS.) and esd adj protection and bipolar adj transistor) and ((base near7 (surround\$3 or enclos\$3)) near7 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:39
-	1115	((("257/360") or ("257/361") or ("257/362") or ("257/363")).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:38
-	122	((("257/360") or ("257/361") or ("257/362") or ("257/363")).CCLS.) and esd adj protection and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:39
-	6	((("257/360") or ("257/361") or ("257/362") or ("257/363")).CCLS.) and esd adj protection and bipolar adj transistor) and ((base near7 (surround\$3 or enclos\$3)) near7 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:42
-	893	((("257/370") or ("257/373")).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:41
-	7	((("257/370") or ("257/373")).CCLS.) and esd adj protection and bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 17:42
-	0	((("257/370") or ("257/373")).CCLS.) and esd adj protection and bipolar adj transistor) and ((base near7 (surround\$3 or enclos\$3)) near7 (emitter or collector))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 18:25
-	192	bipolar adj transistor.ti,ab. and second adj2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 18:28
-	65	bipolar adj transistor.ti. and second adj2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 18:42
-	2	lateral adj bipolar adj transistor.ti. and second adj2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 18:45
-	15	lateral adj bipolar adj transistor.ti,ab. and second adj2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/06 18:45
-	0	(source or drain) adj regions same through-contact\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/07 08:33

-	3	formed adj2 "same substrate" same plurality adj2 bipolar adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/07 10:01
-	4	((("5623387") or ("5043782") or ("6075271") or ("6277689"))).PN.	USPAT	2002/02/07 10:02
-	0	jp-0361292351\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/07 10:04
-	0	jp-361292351\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/07 10:04
-	2	jp-61292351\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/07 10:04